Intel - EPF10K50VQC240-2N Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	20480
Number of I/O	189
Number of Gates	116000
Voltage - Supply	3V ~ 3.6V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	240-BFQFP
Supplier Device Package	240-PQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k50vqc240-2n

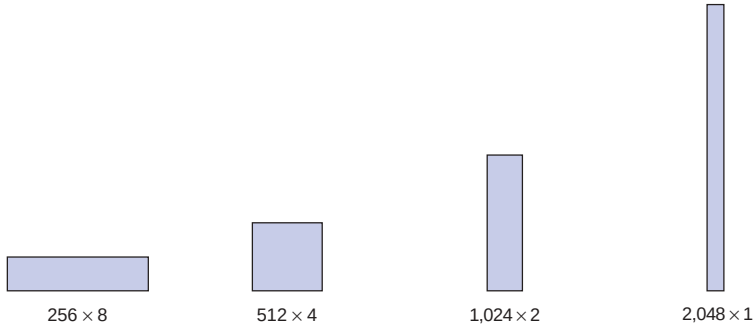
Logic functions are implemented by programming the EAB with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement a 4 × 4 multiplier with eight inputs and eight outputs. Parameterized functions such as LPM functions can automatically take advantage of the EAB.

The EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These FPGA RAM blocks contain delays that are less predictable as the size of the RAM increases. In addition, FPGA RAM blocks are prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

EABs can be used to implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the EAB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. A circuit using the EAB's self-timed RAM need only meet the setup and hold time specifications of the global clock.

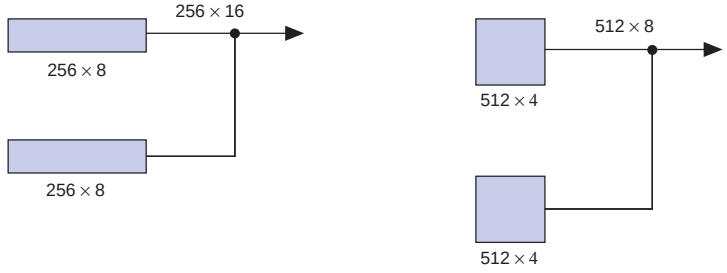
When used as RAM, each EAB can be configured in any of the following sizes: 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. See Figure 2.

Figure 2. EAB Memory Configurations



Larger blocks of RAM are created by combining multiple EABs. For example, two 256 × 8 RAM blocks can be combined to form a 256 × 16 RAM block; two 512 × 4 blocks of RAM can be combined to form a 512 × 8 RAM block. See Figure 3.

Figure 3. Examples of Combining EABs

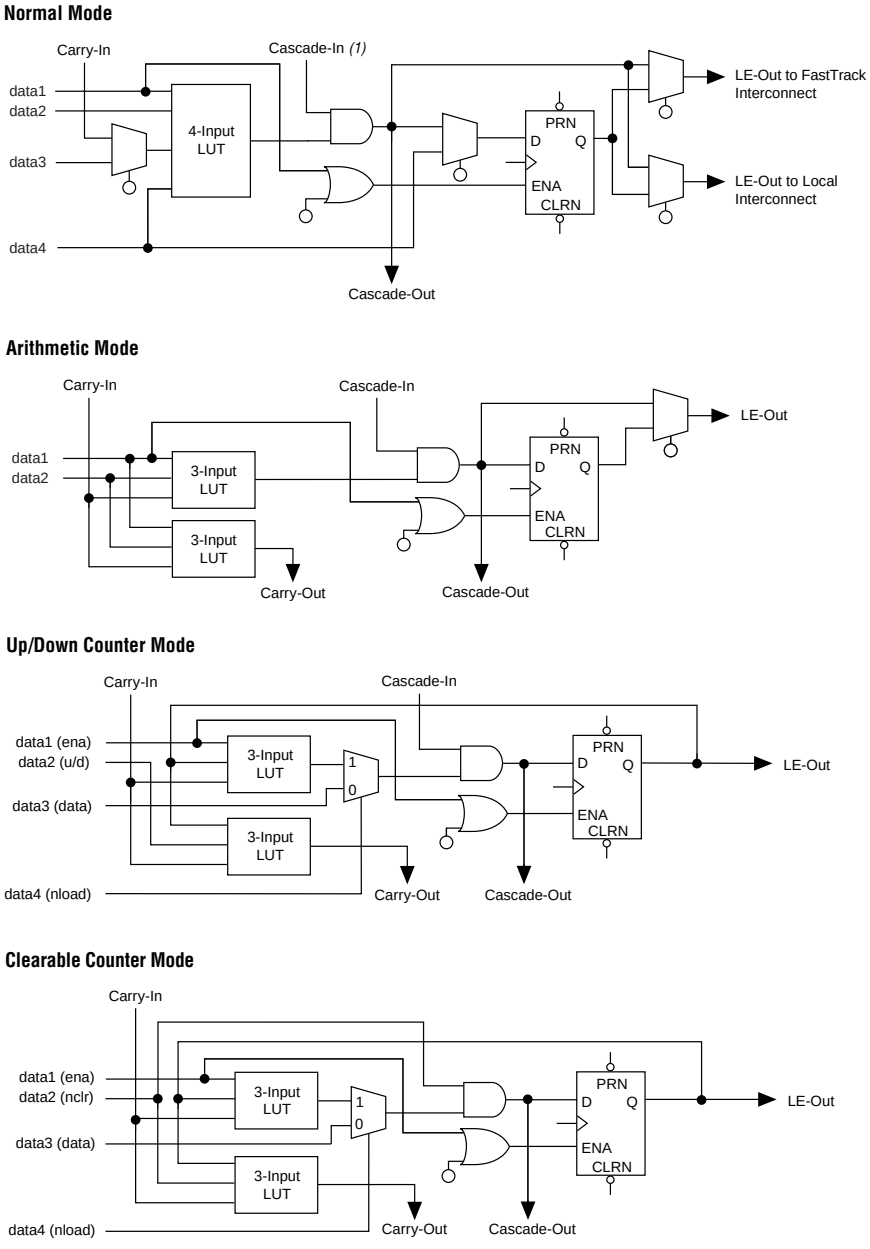


If necessary, all EABs in a device can be cascaded to form a single RAM block. EABs can be cascaded to form RAM blocks of up to 2,048 words without impacting timing. Altera's software automatically combines EABs to meet a designer's RAM specifications.

EABs provide flexible options for driving and controlling clock signals. Different clocks can be used for the EAB inputs and outputs. Registers can be independently inserted on the data input, EAB output, or the address and `WE` inputs. The global signals and the EAB local interconnect can drive the `WE` signal. The global signals, dedicated clock pins, and EAB local interconnect can drive the EAB clock signals. Because the LEs drive the EAB local interconnect, the LEs can control the `WE` signal or the EAB clock signals.

Each EAB is fed by a row interconnect and can drive out to row and column interconnects. Each EAB output can drive up to two row channels and up to two column channels; the unused row channel can be driven by other LEs. This feature increases the routing resources available for EAB outputs. See Figure 4.

Figure 9. FLEX 10K LE Operating Modes



Note:
(1) Packed registers cannot be used with the cascade chain.

Figure 12 shows the interconnection of adjacent LABs and EABs with row, column, and local interconnects, as well as the associated cascade and carry chains. Each LAB is labeled according to its location: a letter represents the row and a number represents the column. For example, LAB B3 is in row B, column 3.

Figure 12. Interconnect Resources

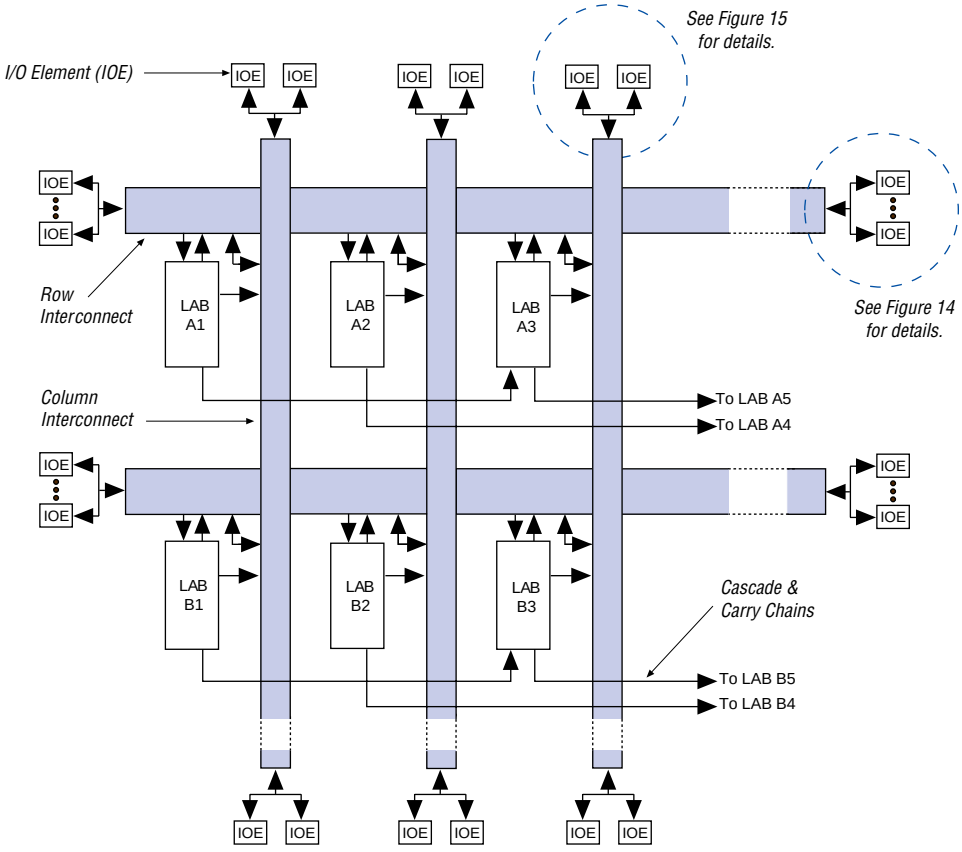


Table 8. EPF10K10, EPF10K20, EPF10K30, EPF10K40 & EPF10K50 Peripheral Bus Sources

Peripheral Control Signal	EPF10K10 EPF10K10A	EPF10K20	EPF10K30 EPF10K30A	EPF10K40	EPF10K50 EPF10K50V
OE0	Row A	Row A	Row A	Row A	Row A
OE1	Row A	Row B	Row B	Row C	Row B
OE2	Row B	Row C	Row C	Row D	Row D
OE3	Row B	Row D	Row D	Row E	Row F
OE4	Row C	Row E	Row E	Row F	Row H
OE5	Row C	Row F	Row F	Row G	Row J
CLKENA0/CLK0/GLOBAL0	Row A	Row A	Row A	Row B	Row A
CLKENA1/OE6/GLOBAL1	Row A	Row B	Row B	Row C	Row C
CLKENA2/CLR0	Row B	Row C	Row C	Row D	Row E
CLKENA3/OE7/GLOBAL2	Row B	Row D	Row D	Row E	Row G
CLKENA4/CLR1	Row C	Row E	Row E	Row F	Row I
CLKENA5/CLK1/GLOBAL3	Row C	Row F	Row F	Row H	Row J

Table 9. EPF10K70, EPF10K100, EPF10K130V & EPF10K250A Peripheral Bus Sources

Peripheral Control Signal	EPF10K70	EPF10K100 EPF10K100A	EPF10K130V	EPF10K250A
OE0	Row A	Row A	Row C	Row E
OE1	Row B	Row C	Row E	Row G
OE2	Row D	Row E	Row G	Row I
OE3	Row I	Row L	Row N	Row P
OE4	Row G	Row I	Row K	Row M
OE5	Row H	Row K	Row M	Row O
CLKENA0/CLK0/GLOBAL0	Row E	Row F	Row H	Row J
CLKENA1/OE6/GLOBAL1	Row C	Row D	Row F	Row H
CLKENA2/CLR0	Row B	Row B	Row D	Row F
CLKENA3/OE7/GLOBAL2	Row F	Row H	Row J	Row L
CLKENA4/CLR1	Row H	Row J	Row L	Row N
CLKENA5/CLK1/GLOBAL3	Row E	Row G	Row I	Row K

Signals on the peripheral control bus can also drive the four global signals, referred to as GLOBAL0 through GLOBAL3 in Tables 8 and 9. The internally generated signal can drive the global signal, providing the same low-skew, low-delay characteristics for an internally generated signal as for a signal driven by an input. This feature is ideal for internally generated clear or clock signals with high fan-out. When a global signal is driven by internal logic, the dedicated input pin that drives that global signal cannot be used. The dedicated input pin should be driven to a known logic state (such as ground) and not be allowed to float.

When the chip-wide output enable pin is held low, it will tri-state all pins on the device. This option can be set in the Global Project Device Options menu. Additionally, the registers in the IOE can be reset by holding the chip-wide reset pin low.

Row-to-IOE Connections

When an IOE is used as an input signal, it can drive two separate row channels. The signal is accessible by all LEs within that row. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the row channels. Up to eight IOEs connect to each side of each row channel. See Figure 14.

Figure 14. FLEX 10K Row-to-IOE Connections

The values for m and n are provided in Table 10.

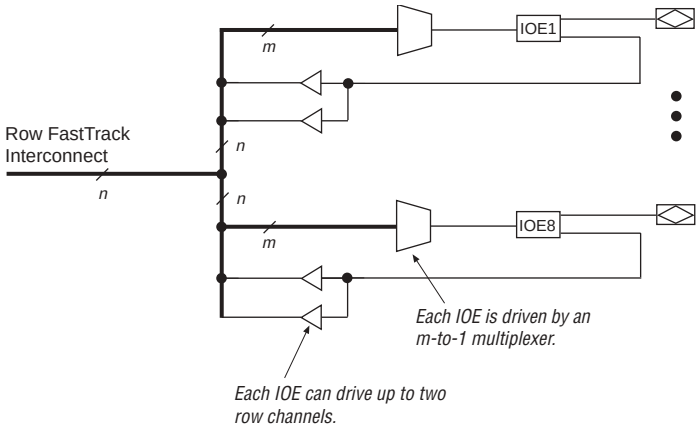


Figure 18 shows the timing requirements for the JTAG signals.

Figure 18. JTAG Waveforms

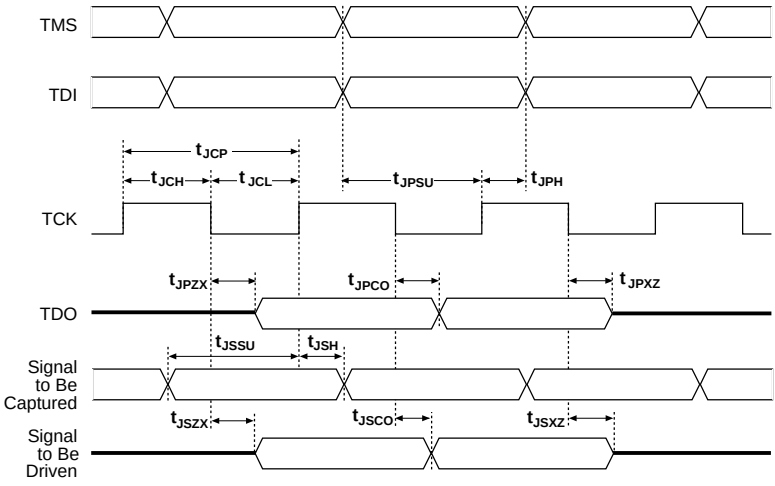


Table 16 shows the timing parameters and values for FLEX 10K devices.

Table 16. JTAG Timing Parameters & Values

Symbol	Parameter	Min	Max	Unit
t_{JCP}	TCK clock period	100		ns
t_{JCH}	TCK clock high time	50		ns
t_{JCL}	TCK clock low time	50		ns
t_{JPSU}	JTAG port setup time	20		ns
t_{JPH}	JTAG port hold time	45		ns
t_{JPCO}	JTAG port clock to output		25	ns
t_{JPZX}	JTAG port high impedance to valid output		25	ns
t_{JPXZ}	JTAG port valid output to high impedance		25	ns
t_{JSSU}	Capture register setup time	20		ns
t_{JSH}	Capture register hold time	45		ns
t_{JSCO}	Update register clock to output		35	ns
t_{JSZX}	Update register high-impedance to valid output		35	ns
t_{JSXZ}	Update register valid output to high impedance		35	ns

Table 18. FLEX 10K 5.0-V Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	4.75 (4.50)	5.25 (5.50)	V
V_{CCIO}	Supply voltage for output buffers, 5.0-V operation	*(3)*, *(4)*	4.75 (4.50)	5.25 (5.50)	V
	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
V_I	Input voltage		–0.5	V_{CCINT} + 0.5	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	° C
		For industrial use	–40	85	° C
T_J	Operating temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 19. FLEX 10K 5.0-V Device DC Operating Conditions *Notes (5), (6)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		2.0		V_{CCINT} + 0.5	V
V_{IL}	Low-level input voltage		–0.5		0.8	V
V_{OH}	5.0-V high-level TTL output voltage	I_{OH} = –4 mA DC, V_{CCIO} = 4.75 V *(7)*	2.4			V
	3.3-V high-level TTL output voltage	I_{OH} = –4 mA DC, V_{CCIO} = 3.00 V *(7)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(7)*	V_{CCIO} – 0.2			V
V_{OL}	5.0-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 4.75 V *(8)*			0.45	V
	3.3-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(8)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(8)*			0.2	V
I_I	Input pin leakage current	V_I = V_{CC} or ground *(9)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = V_{CC} or ground *(9)*	–40		40	µA
I_{CC0}	V_{CC} supply current (standby)	V_I = ground, no load		0.5	10	mA

Table 20. 5.0-V Device Capacitance of EPF10K10, EPF10K20 & EPF10K30 Devices *Note (10)*

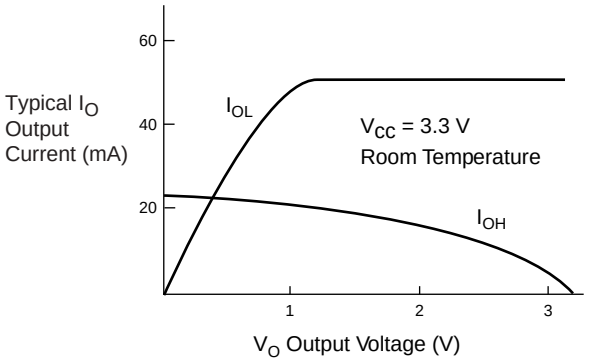
Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Table 21. 5.0-V Device Capacitance of EPF10K40, EPF10K50, EPF10K70 & EPF10K100 Devices *Note (10)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		10	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		15	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		10	pF

Figure 21 shows the typical output drive characteristics of EPF10K50V and EPF10K130V devices.

Figure 21. Output Drive Characteristics of EPF10K50V & EPF10K130V Devices

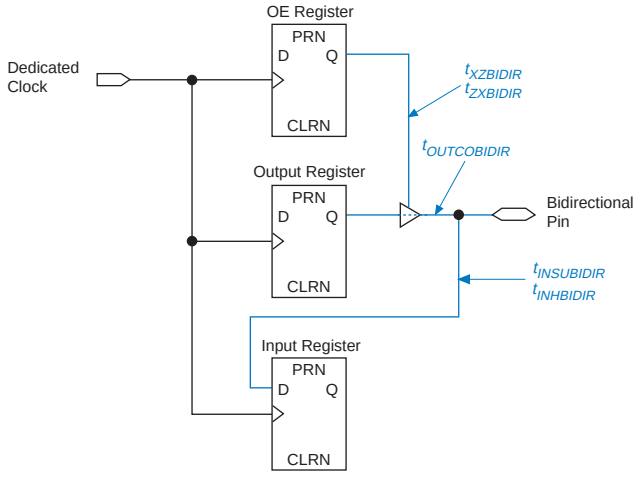


Tables 26 through 31 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 3.3-V FLEX 10K devices.

Table 26. FLEX 10KA 3.3-V Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	Supply voltage	With respect to ground *(2)*	–0.5	4.6	V
V_I	DC input voltage		–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	Ceramic packages, under bias		150	° C
		PQFP, TQFP, RQFP, and BGA packages, under bias		135	° C

Figure 28. Synchronous Bidirectional Pin External Timing Model



Tables 32 through 36 describe the FLEX 10K device internal timing parameters. These internal timing parameters are expressed as worst-case values. Using hand calculations, these parameters can be used to estimate design performance. However, before committing designs to silicon, actual worst-case performance should be modeled using timing simulation and analysis. Tables 37 through 38 describe FLEX 10K external timing parameters.

Table 32. LE Timing Microparameters (Part 1 of 2) *Note (1)*

Symbol	Parameter	Conditions
t_{LUT}	LUT delay for data-in	
t_{CLUT}	LUT delay for carry-in	
t_{RLUT}	LUT delay for LE register feedback	
t_{PACKED}	Data-in to packed register delay	
t_{EN}	LE register enable delay	
t_{CICO}	Carry-in to carry-out delay	
t_{CGEN}	Data-in to carry-out delay	
t_{CGENR}	LE register feedback to carry-out delay	
t_{CASC}	Cascade-in to cascade-out delay	
t_{C}	LE register control signal delay	
t_{CO}	LE register clock-to-output delay	
t_{COMB}	Combinatorial delay	

Table 35. EAB Timing Macroparameters *Notes (1), (6)*		
Symbol	**Parameter**	**Conditions**
t_{EABAA}	EAB address access delay	
$t_{EABRCCOMB}$	EAB asynchronous read cycle time	
$t_{EABRCREG}$	EAB synchronous read cycle time	
t_{EABWP}	EAB write pulse width	
$t_{EABWCCOMB}$	EAB asynchronous write cycle time	
$t_{EABWCREG}$	EAB synchronous write cycle time	
t_{EABDD}	EAB data-in to data-out valid delay	
$t_{EABDATACO}$	EAB clock-to-output delay when using output registers	
$t_{EABDATASU}$	EAB data/address setup time before clock when using input register	
$t_{EABDATAH}$	EAB data/address hold time after clock when using input register	
$t_{EABWESU}$	EAB WE setup time before clock when using input register	
t_{EABWEH}	EAB WE hold time after clock when using input register	
$t_{EABWDSU}$	EAB data setup time before falling edge of write pulse when not using input registers	
t_{EABWDH}	EAB data hold time after falling edge of write pulse when not using input registers	
$t_{EABWASU}$	EAB address setup time before rising edge of write pulse when not using input registers	
t_{EABWAH}	EAB address hold time after falling edge of write pulse when not using input registers	
t_{EABWO}	EAB write enable to data output valid delay	

Table 41. EPF10K10 & EPF10K20 Device EAB Internal Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		1.9	ns
$t_{EABDATA2}$		4.8		6.0	ns
t_{EABWE1}		1.0		1.2	ns
t_{EABWE2}		5.0		6.2	ns
t_{EABCLK}		1.0		2.2	ns
t_{EABCO}		0.5		0.6	ns
$t_{EABBYPASS}$		1.5		1.9	ns
t_{EABSU}	1.5		1.8		ns
t_{EABH}	2.0		2.5		ns
t_{AA}		8.7		10.7	ns
t_{WP}	5.8		7.2		ns
t_{WDSU}	1.6		2.0		ns
t_{WDH}	0.3		0.4		ns
t_{WASU}	0.5		0.6		ns
t_{WAH}	1.0		1.2		ns
t_{WO}		5.0		6.2	ns
t_{DD}		5.0		6.2	ns
t_{EABOUT}		0.5		0.6	ns
t_{EABCH}	4.0		4.0		ns
t_{EABCL}	5.8		7.2		ns

Table 51. EPF10K30, EPF10K40 & EPF10K50 Device EAB Internal Timing Macroparameters *Note (1)*					
Symbol	**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	
t_{EABAA}		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		17.0		ns
$t_{EABRCREG}$	9.7		11.9		ns
t_{EABWP}	5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		9.0		ns
$t_{EABWCREG}$	13.0		16.0		ns
t_{EABDD}		10.0		12.5	ns
$t_{EABDATACO}$		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		ns
$t_{EABWESU}$	5.5		5.8		ns
t_{EABWEH}	0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.8		ns
t_{EABWDH}	0.0		0.0		ns
$t_{EABWASU}$	2.1		2.7		ns
t_{EABWAH}	0.0		0.0		ns
t_{EABWO}		9.5		11.8	ns

Tables 71 through 77 show EPF10K50V device internal and external timing parameters.

Table 71. EPF10K50V Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.9		1.0		1.3		1.6	ns
t_{CLUT}		0.1		0.5		0.6		0.6	ns
t_{RLUT}		0.5		0.8		0.9		1.0	ns
t_{PACKED}		0.4		0.4		0.5		0.7	ns
t_{EN}		0.7		0.9		1.1		1.4	ns
t_{CICO}		0.2		0.2		0.2		0.3	ns
t_{CGEN}		0.8		0.7		0.8		1.2	ns
t_{CGENR}		0.4		0.3		0.3		0.4	ns
t_{CASC}		0.7		0.7		0.8		0.9	ns
t_{C}		0.3		1.0		1.3		1.5	ns
t_{CO}		0.5		0.7		0.9		1.0	ns
t_{COMB}		0.4		0.4		0.5		0.6	ns
t_{SU}	0.8		1.6		2.2		2.5		ns
t_{H}	0.5		0.8		1.0		1.4		ns
t_{PRE}		0.8		0.4		0.5		0.5	ns
t_{CLR}		0.8		0.4		0.5		0.5	ns
t_{CH}	2.0		4.0		4.0		4.0		ns
t_{CL}	2.0		4.0		4.0		4.0		ns

Table 72. EPF10K50V Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.2		1.6		1.9		2.1	ns
t_{IOC}		0.3		0.4		0.5		0.5	ns
t_{IOCO}		0.3		0.3		0.4		0.4	ns
t_{IOCOMB}		0.0		0.0		0.0		0.0	ns
t_{IOSU}	2.8		2.8		3.4		3.9		ns
t_{IOH}	0.7		0.8		1.0		1.4		ns
t_{IOCLR}		0.5		0.6		0.7		0.7	ns
t_{OD1}		2.8		3.2		3.9		4.7	ns
t_{OD2}		–		–		–		–	ns
t_{OD3}		6.5		6.9		7.6		8.4	ns
t_{XZ}		2.8		3.1		3.8		4.6	ns
t_{ZX1}		2.8		3.1		3.8		4.6	ns
t_{ZX2}		–		–		–		–	ns
t_{ZX3}		6.5		6.8		7.5		8.3	ns
t_{INREG}		5.0		5.7		7.0		9.0	ns
t_{IOFD}		1.5		1.9		2.3		2.7	ns
t_{INCOMB}		1.5		1.9		2.3		2.7	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 78 through 84 show EPF10K130V device internal and external timing parameters.

Table 78. EPF10K130V Device LE Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.3		1.8		2.3	ns
t_{CLUT}		0.5		0.7		0.9	ns
t_{RLUT}		1.2		1.7		2.2	ns
t_{PACKED}		0.5		0.6		0.7	ns
t_{EN}		0.6		0.8		1.0	ns
t_{CICO}		0.2		0.3		0.4	ns
t_{CGEN}		0.3		0.4		0.5	ns
t_{CGENR}		0.7		1.0		1.3	ns
t_{CASC}		0.9		1.2		1.5	ns
t_{C}		1.9		2.4		3.0	ns
t_{CO}		0.6		0.9		1.1	ns
t_{COMB}		0.5		0.7		0.9	ns
t_{SU}	0.2		0.2		0.3		ns
t_{H}	0.0		0.0		0.0		ns
t_{PRE}		2.4		3.1		3.9	ns
t_{CLR}		2.4		3.1		3.9	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 80. EPF10K130V Device EAB Internal Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.9		2.4		2.4	ns
$t_{EABDATA2}$		3.7		4.7		4.7	ns
t_{EABWE1}		1.9		2.4		2.4	ns
t_{EABWE2}		3.7		4.7		4.7	ns
t_{EABCLK}		0.7		0.9		0.9	ns
t_{EABCO}		0.5		0.6		0.6	ns
$t_{EABBYPASS}$		0.6		0.8		0.8	ns
t_{EABSU}	1.4		1.8		1.8		ns
t_{EABH}	0.0		0.0		0.0		ns
t_{AA}		5.6		7.1		7.1	ns
t_{WP}	3.7		4.7		4.7		ns
t_{WDSU}	4.6		5.9		5.9		ns
t_{WDH}	0.0		0.0		0.0		ns
t_{WASU}	3.9		5.0		5.0		ns
t_{WAH}	0.0		0.0		0.0		ns
t_{WO}		5.6		7.1		7.1	ns
t_{DD}		5.6		7.1		7.1	ns
t_{EABOUT}		2.4		3.1		3.1	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	4.0		4.7		4.7		ns

Table 87. EPF10K10A Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		3.3		3.9		5.2	ns
$t_{EABDATA2}$		1.0		1.3		1.7	ns
t_{EABWE1}		2.6		3.1		4.1	ns
t_{EABWE2}		2.7		3.2		4.3	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		1.2		1.4		1.8	ns
$t_{EABBYPASS}$		0.1		0.2		0.2	ns
t_{EABSU}	1.4		1.7		2.2		ns
t_{EABH}	0.1		0.1		0.1		ns
t_{AA}		4.5		5.4		7.3	ns
t_{WP}	2.0		2.4		3.2		ns
t_{WDSU}	0.7		0.8		1.1		ns
t_{WDH}	0.5		0.6		0.7		ns
t_{WASU}	0.6		0.7		0.9		ns
t_{WAH}	0.9		1.1		1.5		ns
t_{WO}		3.3		3.9		5.2	ns
t_{DD}		3.3		3.9		5.2	ns
t_{EABOUT}		0.1		0.1		0.2	ns
t_{EABCH}	3.0		3.5		4.0		ns
t_{EABCL}	3.03		3.5		4.0		ns

Notes: